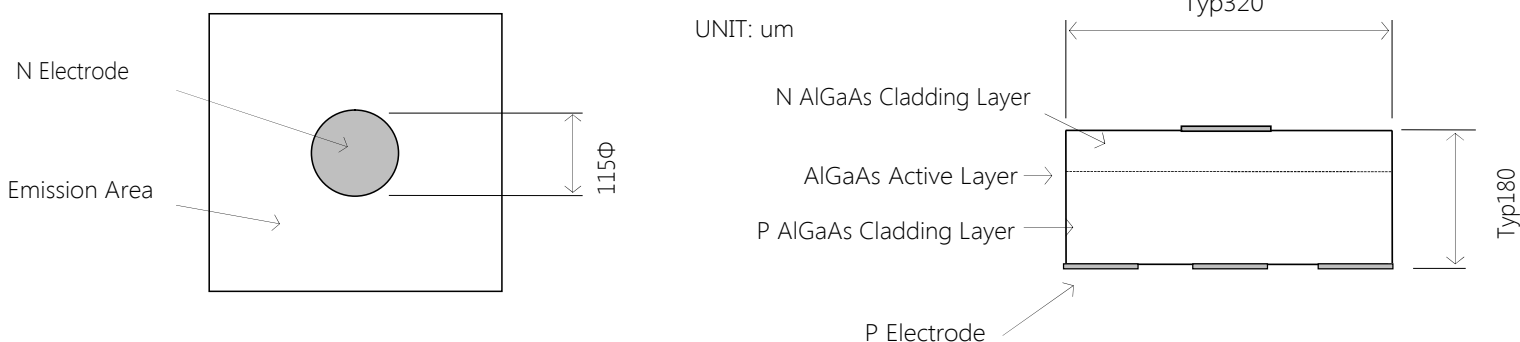


Radiation	Type	Electrodes
Infrared	AlGaAs	N (cathode) up



Physical Characteristics & Structure

Material: AlGaAs	Bond Pad Size: 115 μm diameter
Junction Size: 320 μm x 320 μm	Anode Metalization: Gold Alloy
Thickness: 180 μm	Cathode Metalization: Gold Alloy

Electrical & Optical Characteristics ($T_a = 25^\circ\text{C}$)

ITEMS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage	V_f	$I_f=20\text{mA}$	--	--	1.6	V
Reverse Voltage	V_r	$I_r=10\mu\text{A}$	5	--	--	V
Radiant Power*	Φ_e	$I_f=20\text{mA}$	4.0	--	--	mW
Peak Wavelength	λ_p	$I_f=20\text{mA}$	--	830	--	nm
Spectral Bandwidth at 50%	$\Delta\lambda_{0.5}$	$I_f=20\text{mA}$	--	40	--	nm

* LED chip is mounted on TO-18 gold header without resin coated.

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Continuous Maximum Forward Current: 100mA (DC)
 Reverse Voltage: 5V ($I_R=10\mu\text{A}$)
 Storage Temperature
 while on mylar membrane: 0 to 40 °C
 after removal from mylar membrane: -30 to 100 °C



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.